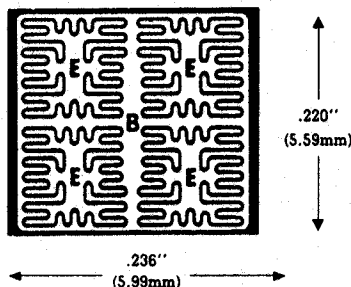


CHIP NUMBER

105



Base: .0155" x .079" (0.39mm x 2.01mm)
 Emitter: .016" x 0.0565" (0.41mm x 1.44mm)

NPN TRIPLE DIFFUSED PLANAR POWER TRANSISTOR

CONTACT METALLIZATION

Base and emitter: > 50,000 Å Aluminum

Collector: Gold

(Polished silicon or "Chrome Nickel Silver" also available)

Also available on:

MOLY PEDESTAL

Size: .375" Diameter (9.53mm)

Thickness: .020" (0.51mm)

BeO PEDESTAL

Size: .250" x .312" (6.35mm x 7.92mm)

Thickness: .042" (1.07mm)

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- a) the chip be eutectically mounted with gold silicon preform 98/2%.
- b) 12 mil (0.305mm) aluminum wire be ultrasonically attached to the base and emitter contacts.

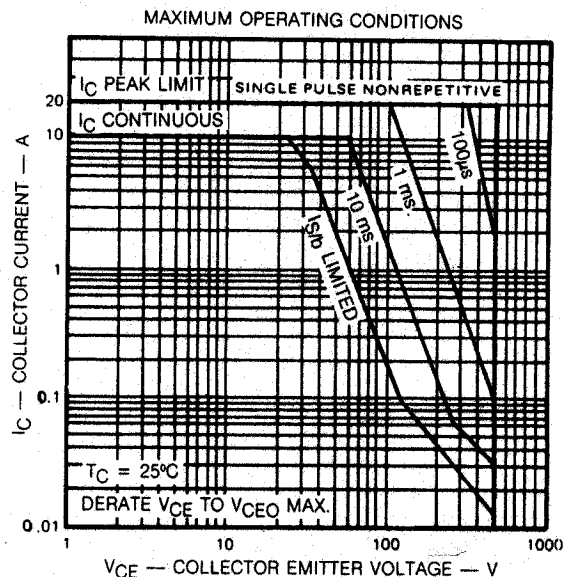
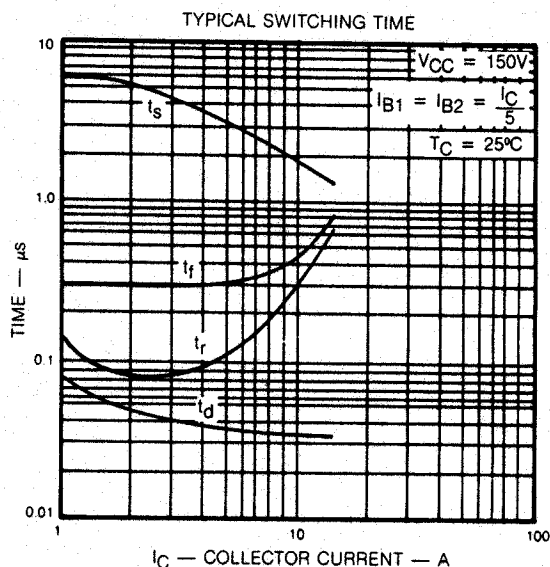
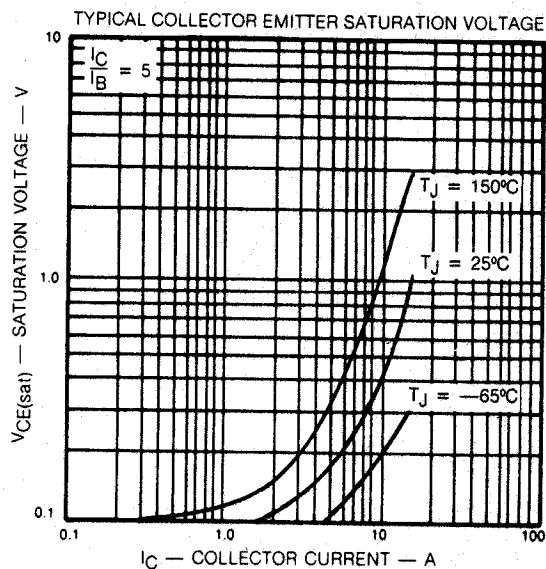
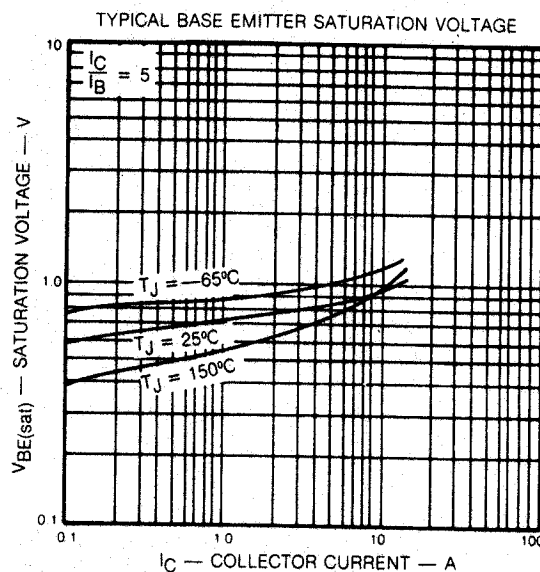
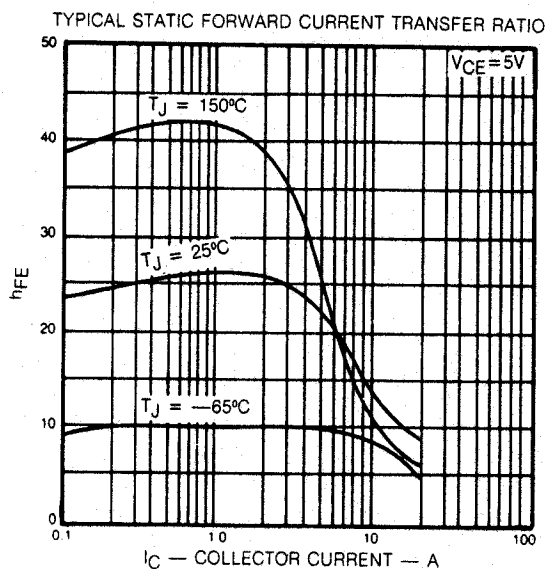
TYPICAL ELECTRICAL CHARACTERISTICS AT 25°C

The following typical electrical characteristics apply for a completely finished component employing the chip number 105 in a TO-3 or equivalent case:

V _{CEO}	V _{CE(s)} @	I _C	I _B	h _{FE} @	I _C	V _{CE}
> 300V	< 1V	5A	0.5A	> 5	15A	5V
> 350V	< 1V	5A	0.5A	> 5	15A	5V
> 400V	< 1V	5A	0.5A	> 5	15A	5V
> 450V	< 1V	5A	0.5A	> 5	15A	5V
> 500V	< 1V	5A	0.5A	> 5	15A	5V

V _{CEO}	V _{CEX}	V _{EBO}	f _T	C _{OBO}	θ _{JC}
> 300V	350V	> 5V	10MHz	< 400pF	< 1.0°C/W
> 350V	400V	> 5V	10MHz	< 400pF	< 1.0°C/W
> 400V	450V	> 5V	10MHz	< 400pF	< 1.0°C/W
> 450V	500V	> 5V	10MHz	< 400pF	< 1.0°C/W
> 500V	550V	> 5V	10MHz	< 400pF	< 1.0°C/W

TYPICAL DEVICE TYPES: JAN2N6546, 2N6547, 2N6561, 2N6563, SDT13301-SDT13305



NOTE:
PERFORMANCE CURVES
REPRESENT LOW TO
MIDDLE CEO VOLTAGE
RANGE OF THIS PRODUCT